

HEX BUFFER/CONVERTERS

4009UB-INVERTING TYPE

4010B-NON INVERTING TYPE

- CMOS TO DTL/TTL HEX CONVERTER
- HIGH-TO-LOW LEVEL LOGIC CONVERSION
- MULTIPLEXER: 1-TO-6 OR 6-TO-1
- HIGH "SINK" AND "SOURCE" CURRENT CAPABILITY
- 5V, 10V AND 15V PARAMETRIC RATINGS
- MAXIMUM INPUT CURRENT OF 100 μ A AT 18V OVER FULL
- PACKAGE AND TEMPERATURE RANGE; 100nA AT 18V AND 25°C
- 100% TESTED FOR QUIESCENT CURRENT AT 20V
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF B SERIES CMOS DEVICES"

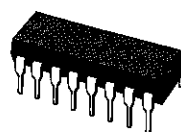
DESCRIPTION

The **HCC4009UB/4010B** (extended temperature range) and the **HCF4009UB/4010B** (intermediate temperature range) are monolithic integrated circuits available in 16-lead dual in line plastic or ceramic packages and plastic micropackage.

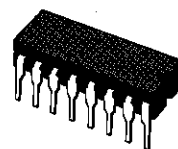
The **HCC/HCF4009UB/4010B** are inverting and

non-inverting Hex Buffer/Converters, respectively. Both devices can be used as CMOS to TTL or DTL logic-level converters, as current "sink" or "source" drivers or as multiplexer (1 to 6).

4049UB and **4050B** are preferred replacements for **4009UB** and **4010B**, respectively, in buffer applications.



EY
(Plastic Package)



F
(Ceramic Package)



M1
(Micro Package)



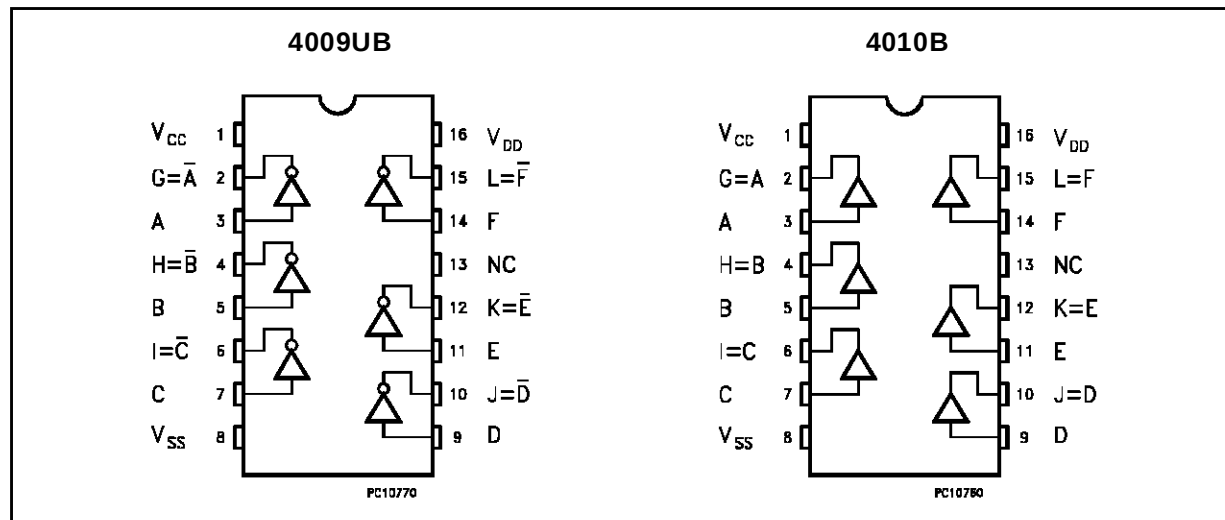
C1
(Chip Carrier)

ORDER CODES :

HCCXXXXBF
HCFXXXXBEY

HCFXXXXBM1
HCFXXXXBC1

PIN CONNECTIONS



STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

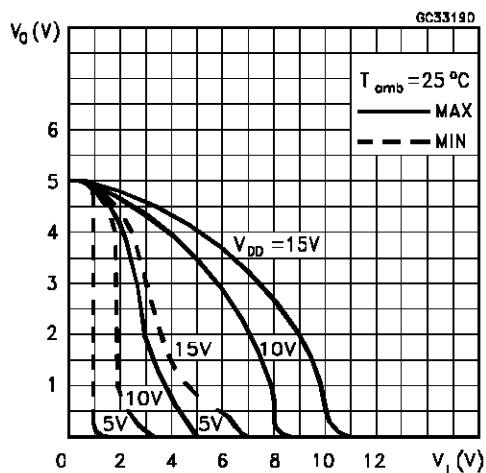
Symbol	Parameter		Test Conditiios				Value							Unit
			V _I (V)	V _O (V)	I _O (μA)	V _{DD} (V)	T _{LOW} *		25 °C			T _{HIGH} *		
							Min.	Max.	Min.	Typ.	Max.	Min.	Max.	
I _L	Quiescent Current	HCC Types	0/5			5		1		0.02	1		30	μA
			0/10			10		2		0.02	2		60	
			0/15			15		4		0.02	4		120	
			0/20			20		20		0.04	20		600	
		HCF Types	0/5			5		4		0.02	4		30	
			0/10			10		8		0.02	8		60	
			0/15			15		16		0.02	16		120	
V _{OH}	Output High Voltage		0/5			5	4.95		4.95			4.95		V
			0/10			10	9.95		9.95			9.95		
			0/15			15	14.95		14.95			14.95		
V _{OL}	Output Low Voltage		5/0			5		0.05			0.05		0.05	V
			10/0			10		0.05			0.05		0.05	
			15/0			15		0.05			0.05		0.05	
V _{IH}	Input High Voltage (4009UB)			0.5		5	4		4			4		V
				1		10	8		8			8		
				1.5		15	12.5		12.5			12.5		
V _{IH}	Input High Voltage (4010B)			4.5		5	3.5		3.5			3.5		V
				9		10	7		7			7		
				13.5		15	11		11			11		
V _{IL}	Input Low Voltage (4009UB)			4.5		5		1			1		1	V
				9		10		2			2		2	
				13.5		15		2.5			2.5		2.5	
V _{IL}	Input Low Voltage (4010B)			0.5		5		1.5			1.5		1.5	V
				1		10		3			3		3	
				1.5		15		4			4		4	
I _{OH}	Output Drive Current	HCC Types	0/5	2.5		5	-1		-0.8	-1.6		-0.58		mA
			0/5	4.6		5	-0.25		-0.2	-0.4		-0.15		
			0/10	9.5		10	-0.55		-0.45	-0.9		-0.33		
			0/15	13.5		15	-1.65		-1.5	-3		-1.1		
		HCF Types	0/5	2.5		5	-0.9		-0.8	-1.6		-0.65		
			0/5	4.6		5	-0.23		-0.2	-0.4		-0.18		
			0/10	9.5		10	-0.5		-0.45	-0.9		-0.38		
			0/15	13.5		15	-1.6		-1.5	-3		-1.25		
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	3.75		3	4		2.1		mA
			0/10	0.5		10	10		8	10		5.6		
			0/15	1.5		15	30		24	36		16		
		HCF Types	0/5	0.4		5	3.6		3	4		2.4		
			0/10	0.5		10	0.96		8	10		6.4		
			0/15	1.5		15	40		24	36		1.9		
I _{IH} , I _{IL}	Input Leakage Current		0/18			18		±0.1		±10 ⁻⁵	±0.1		±1	μA
C _I	Input Capacitance	4009UB		Any Input						15	22.6			pF
		4010B							5	7.5				

* T_{LOW} = -55 °C for HCC device; -40 °C for HCF device.* T_{HIGH} = +125 °C for HCC device; +85 °C for HCF device.The Noise Margin for both "1" and "0" level is: 1V min. with V_{DD} = 5 V, 2 V min. with V_{DD} = 10 V, 2.5 V min. with V_{DD} = 15 V

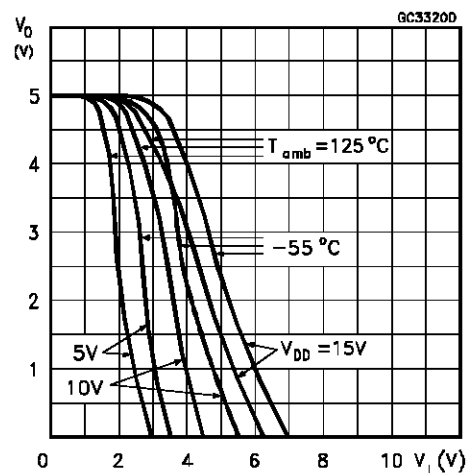
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{ pF}$, $R_L = 200\text{ K}\Omega$, typical temperature coefficient for all V_{DD} values is $03\text{ }^{\circ}\text{C}$, all input rise and fall times = 20 ns)

Symbol	Parameter	Test Conditions			Value			Unit
		V_{DD} (V)	V_I (V)	V_{CC} (V)	Min.	Typ.	Max.	
t_{PLH}	Propagation Delay Time (4009UB)	5	5	5		70	140	ns
		10	10	10		40	80	
		10	10	5		35	70	
		15	15	15		30	60	
		15	15	5		30	60	
t_{PLH}	Propagation Delay Time (4010B)	5	5	5		100	200	ns
		10	10	10		50	100	
		10	10	5		50	100	
		15	15	15		35	70	
		15	15	5		35	70	
t_{PHL}	Propagation Delay Time (4009UB)	5	5	5		30	60	ns
		10	10	10		20	40	
		10	10	5		15	30	
		15	15	15		15	30	
		15	15	5		10	20	
t_{PHL}	Propagation Delay Time (4010B)	5	5	5		65	130	ns
		10	10	10		35	70	
		10	10	5		30	70	
		15	15	15		25	50	
		15	15	5		20	40	
t_{TLH}	Transition Time	5	5	5		150	350	ns
		10	10	10		75	150	
		15	15	15		55	110	
t_{THL}	Transition Time	5	5	5		35	70	ns
		10	10	10		20	40	
		15	15	15		15	30	

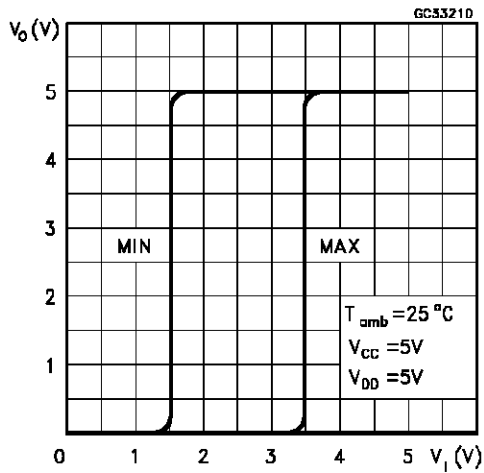
Minimum and Maximum Voltage Transfer Characteristics for 4009UB



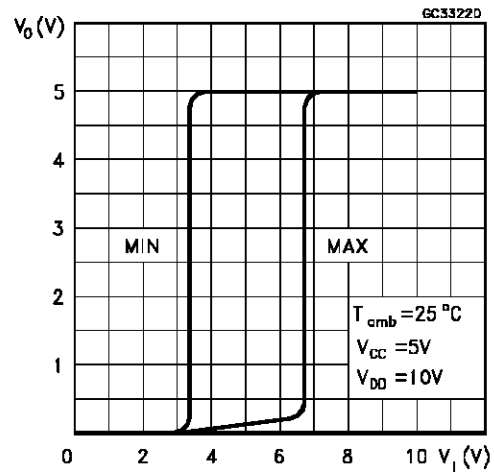
Typical Voltage Transfer Characteristics As a Function of Temperature for 4009UB



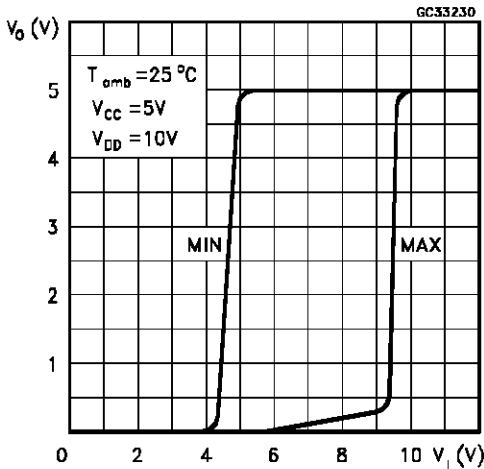
Minimum and Maximum Voltage Transfer Characteristics for 4010B



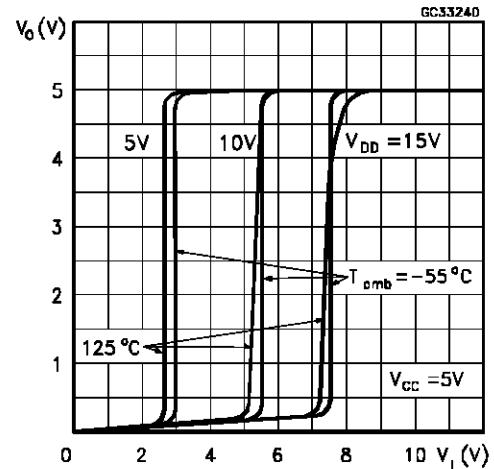
Minimum and Maximum Voltage Transfer Characteristics for 4010B



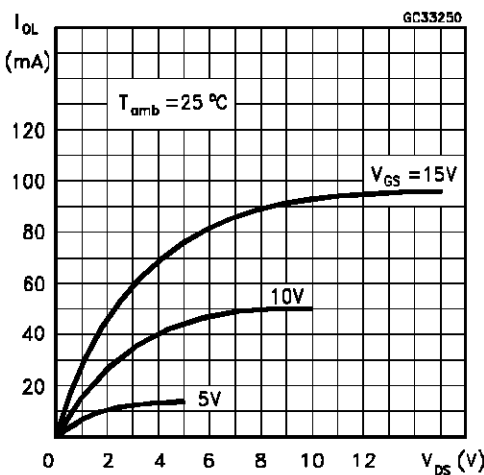
Minimum and Maximum Voltage Transfer Characteristics for 4010B



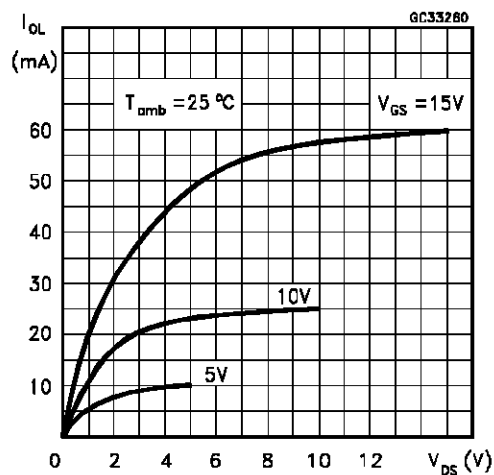
Typical Voltage Transfer Characteristics As a Function of Temperature for 4010B



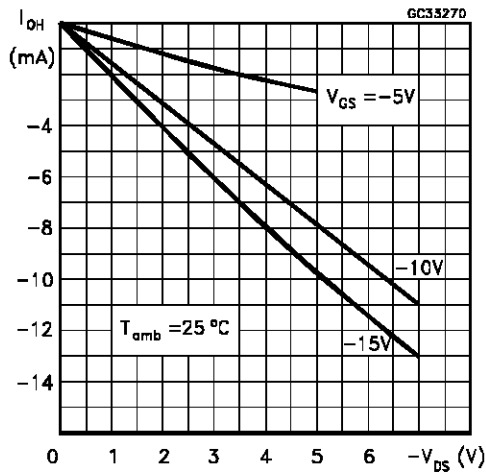
Typical Output Los (sink) Current Characteristics



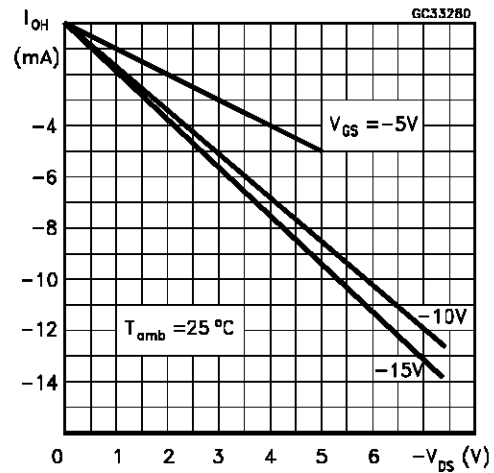
Minimum output Low (sink) Current Characteristics



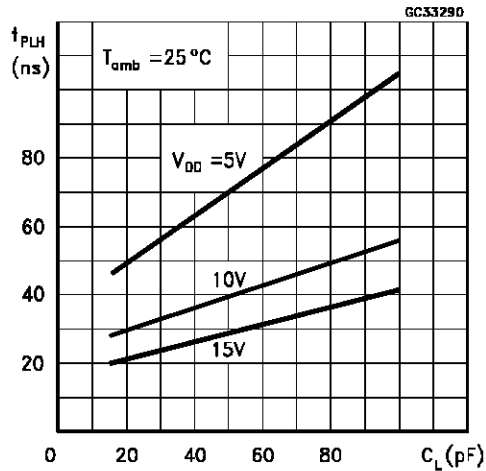
Typical Output High (source) Current Characteristics



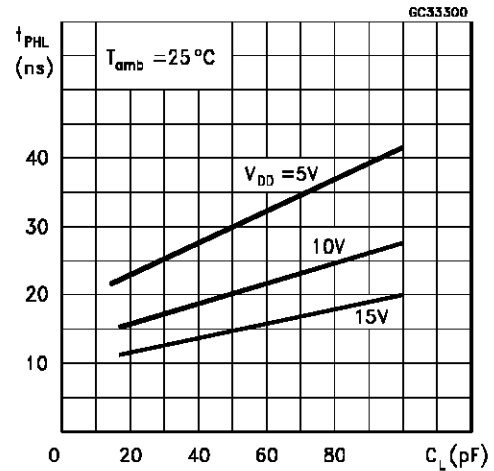
Minimum output High (source) Current Characteristics



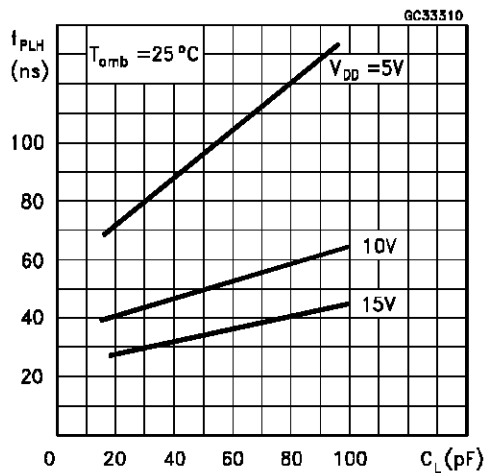
Typical Low to High Propagation Delay Time vs Load Capacitance for 4009UB



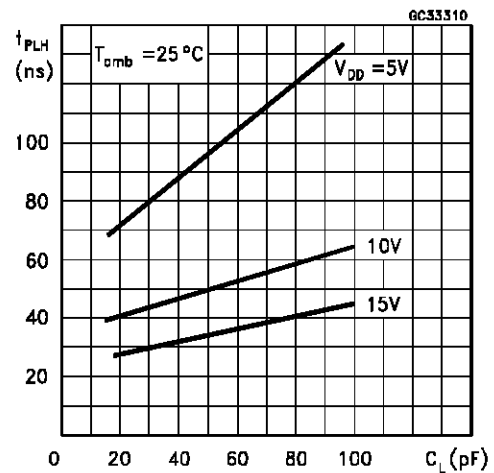
Typical High to Low Propagation Delay Time vs Load Capacitance for 4009UB



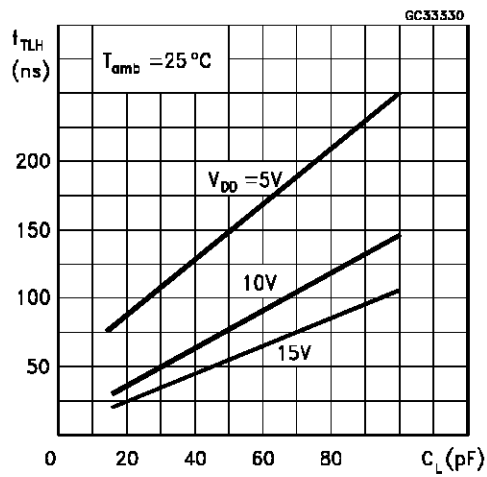
Typical Low to High Propagation Delay Time vs Load Capacitance for 4010B



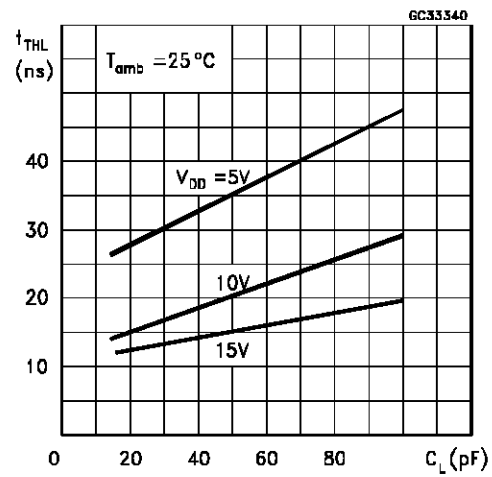
typical High to Low Propagation Delay Time vs Load Capacitance for 4010B



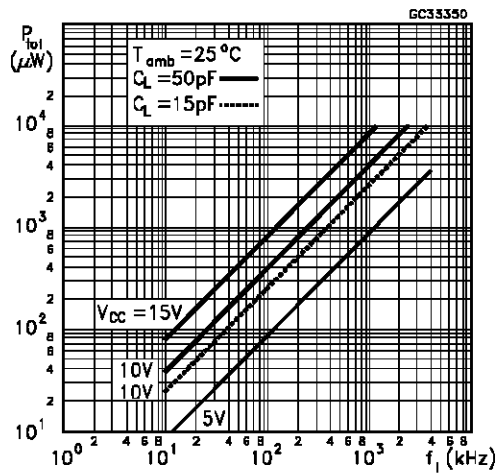
Typical Low to High Transition Time vs Load Capacitance



Typical High to Low Transition Time vs Load Capacitance

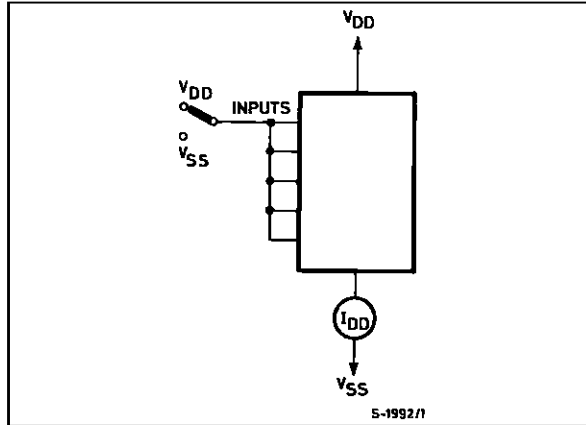


Typical Dissipation Characteristics

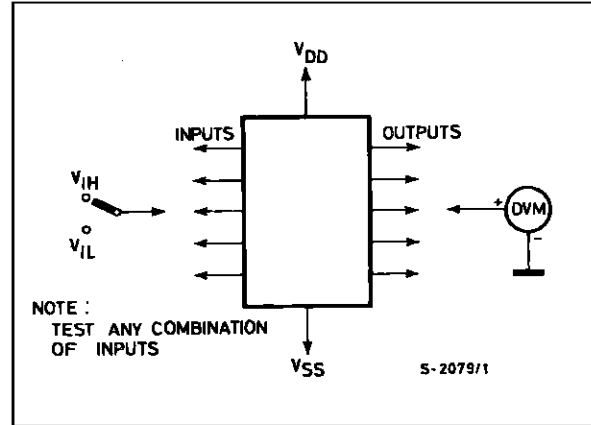


TEST CIRCUITS

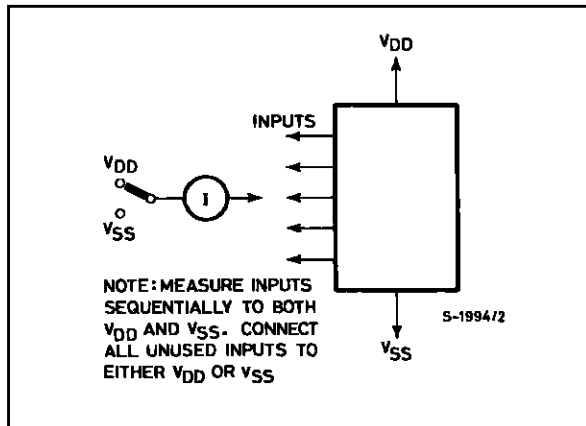
Quiescent Device Current



Noise Immunity.

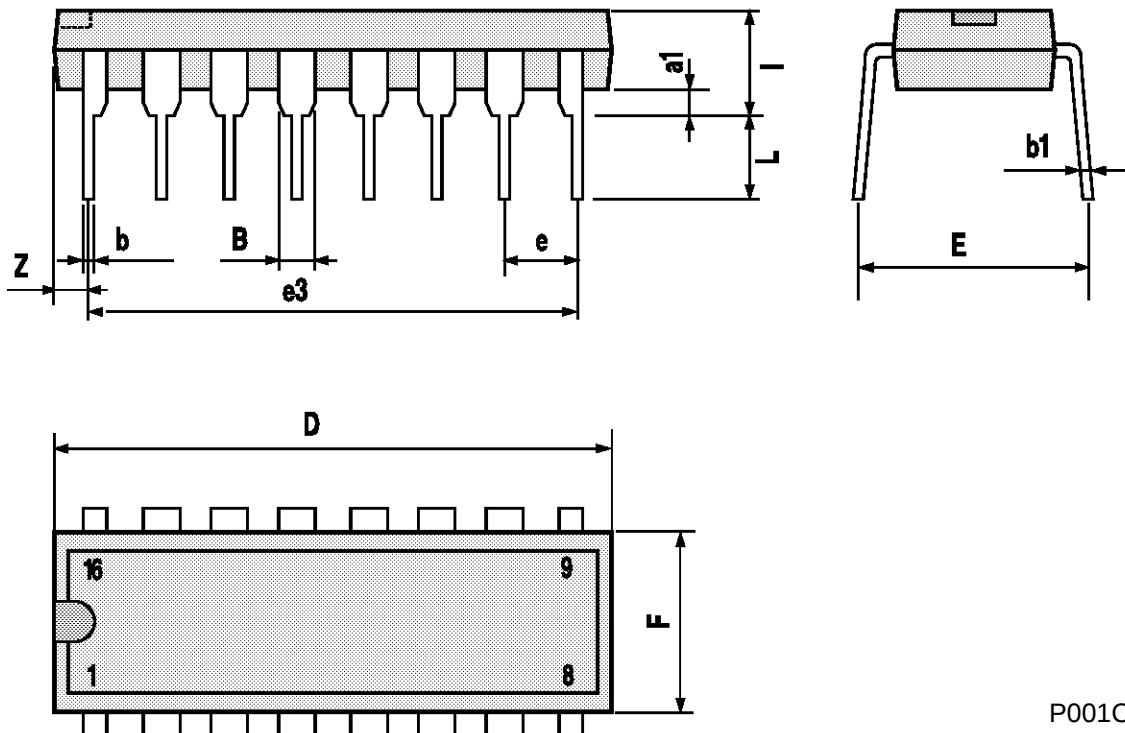


Input Leakage Current.



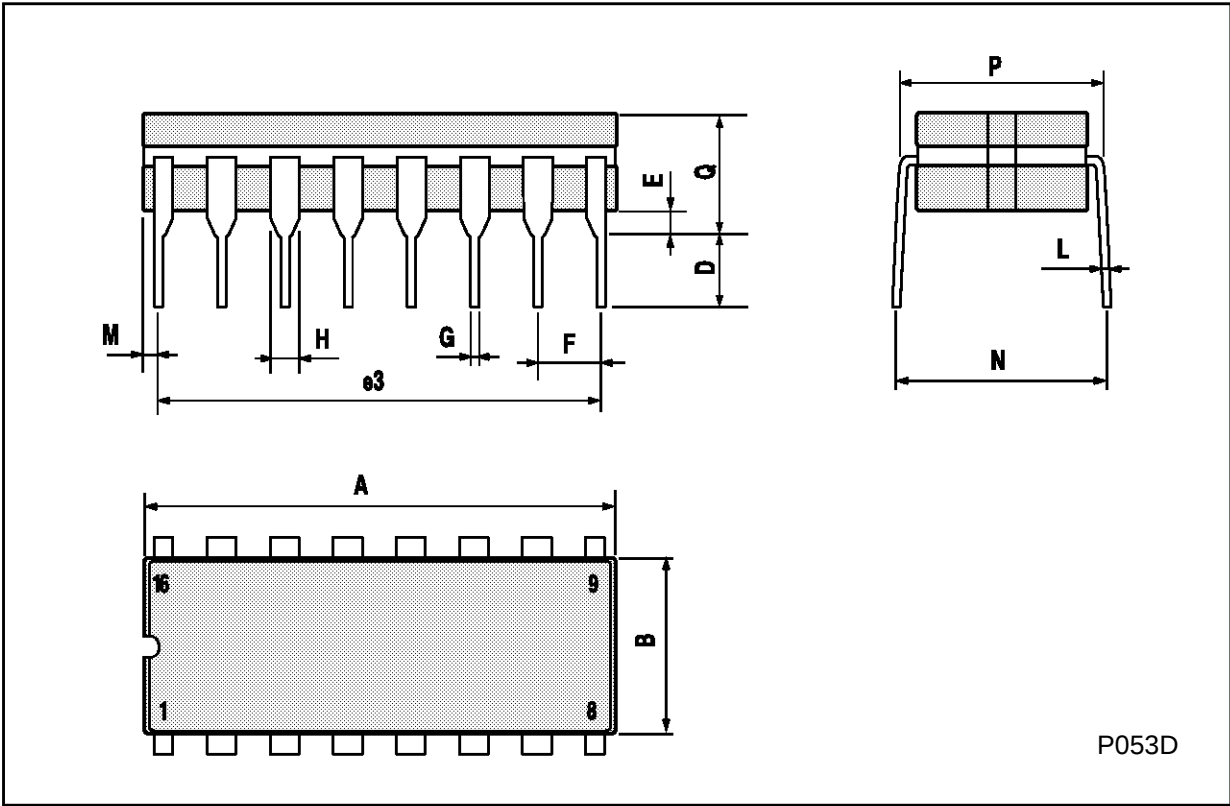
Plastic DIP16 (0.25) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	0.77		1.65	0.030		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		17.78			0.700	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z			1.27			0.050



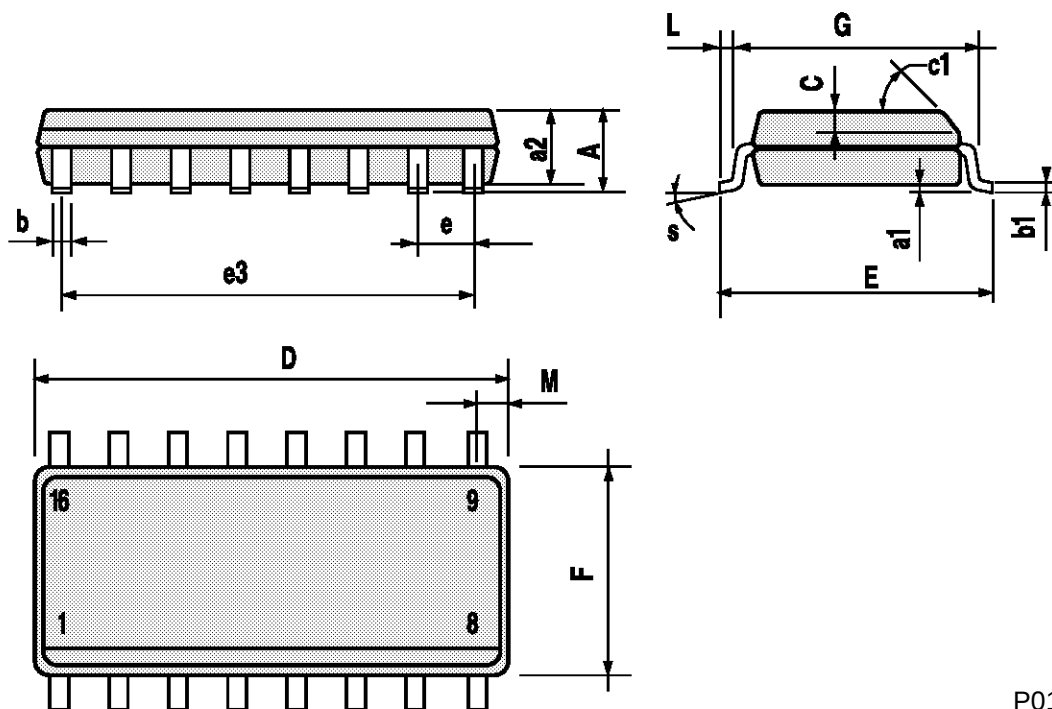
Ceramic DIP16/1 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			20			0.787
B			7			0.276
D		3.3			0.130	
E	0.38			0.015		
e3		17.78			0.700	
F	2.29		2.79	0.090		0.110
G	0.4		0.55	0.016		0.022
H	1.17		1.52	0.046		0.060
L	0.22		0.31	0.009		0.012
M	0.51		1.27	0.020		0.050
N			10.3			0.406
P	7.8		8.05	0.307		0.317
Q			5.08			0.200



SO16 (Narrow) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.004		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	9.8		10	0.385		0.393
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		8.89			0.350	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.62			0.024
S	8° (max.)					



P013H

PLCC20 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	9.78		10.03	0.385		0.395
B	8.89		9.04	0.350		0.356
D	4.2		4.57	0.165		0.180
d1		2.54			0.100	
d2		0.56			0.022	
E	7.37		8.38	0.290		0.330
e		1.27			0.050	
e3		5.08			0.200	
F		0.38			0.015	
G			0.101			0.004
M		1.27			0.050	
M1		1.14			0.045	



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